

# FDP22N50N

## N-Channel UniFET™ II MOSFET

500 V, 22 A, 220 mΩ

### Features

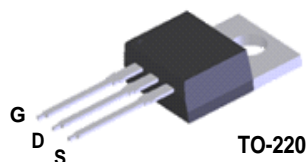
- $R_{DS(on)} = 185 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 11 \text{ A}$
- Low Gate Charge (Typ. 49 nC)
- Low  $C_{rss}$  (Typ. 24 pF)
- 100% Avalanche Tested
- Improve dv/dt Capability
- RoHS Compliant

### Applications

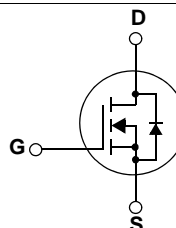
- PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

### Description

UniFET™ II MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.



TO-220



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDP22N50N	Unit
$V_{DSS}$	Drain to Source Voltage	500	V
$V_{GSS}$	Gate to Source Voltage	$\pm 30$	V
$I_D$	Drain Current	-Continuous ( $T_C = 25^\circ\text{C}$ )	A
		-Continuous ( $T_C = 100^\circ\text{C}$ )	
$I_{DM}$	Drain Current	- Pulsed (Note 1)	A
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	V/ns
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	W
		- Derate above $25^\circ\text{C}$	$W/^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FDP22N50N	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP22N50N	FDP22N50N	TO-220	-	-	50

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ ,	500	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.45	-	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 400\text{V}$ , $T_C = 125^\circ\text{C}$	-	-	10	
$I_{GSS}$	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$ , $I_D = 11\text{A}$	-	0.185	0.22	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{V}$ , $I_D = 11\text{A}$	-	24.4	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	2456	3200	pF
$C_{oss}$	Output Capacitance		-	351	460	pF
$C_{rss}$	Reverse Transfer Capacitance		-	24	50	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{V}$ , $I_D = 22\text{A}$ $V_{GS} = 10\text{V}$ (Note 4)	-	49	65	nC
$Q_{gs}$	Gate to Source Gate Charge		-	15	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	19	-	nC

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}$ , $I_D = 22\text{A}$ $R_G = 4.7\Omega$ (Note 4)	-	22	55	ns
$t_r$	Turn-On Rise Time		-	50	110	ns
$t_{d(off)}$	Turn-Off Delay Time		-	48	110	ns
$t_f$	Turn-Off Fall Time		-	35	80	ns

### Drain-Source Diode Characteristics

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	22	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	88	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 22A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>SD</sub> = 22A dI <sub>F</sub> /dt = 100A/μs	-	472	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	6.5	-	μC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 4.1\text{mH}$ ,  $I_{AS} = 22\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 22\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially Independent of Operating Temperature Typical Characteristics

# Typical Performance Characteristics

Figure 1. On-Region Characteristics

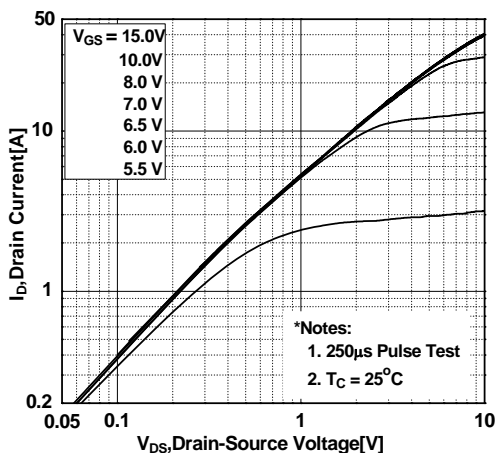


Figure 2. Transfer Characteristics

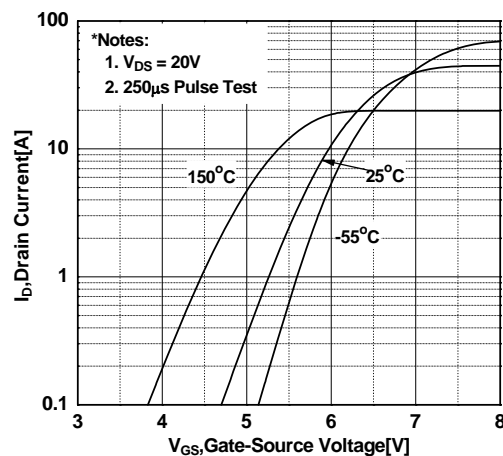


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

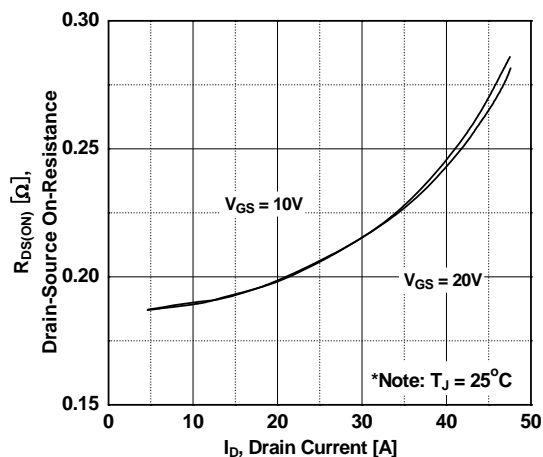


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

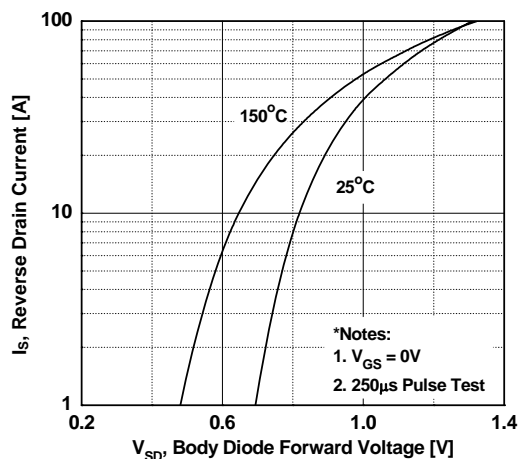


Figure 5. Capacitance Characteristics

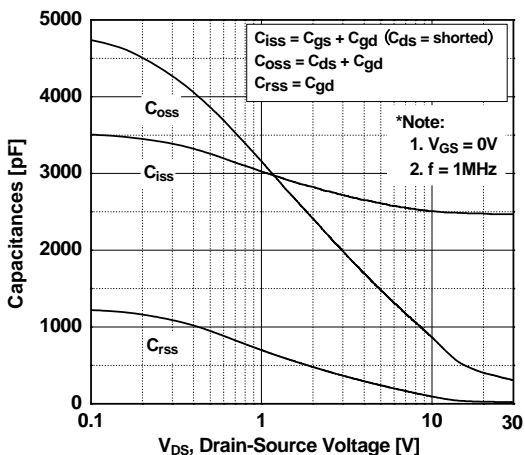
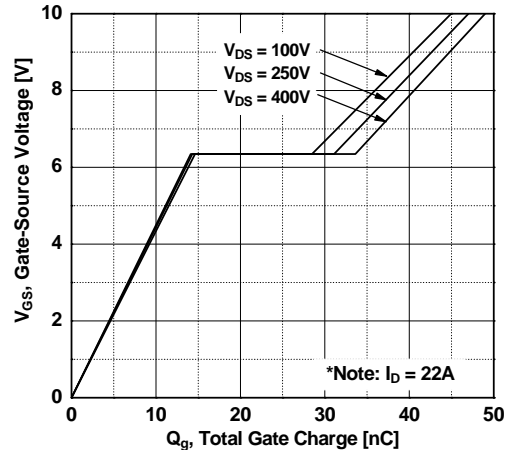
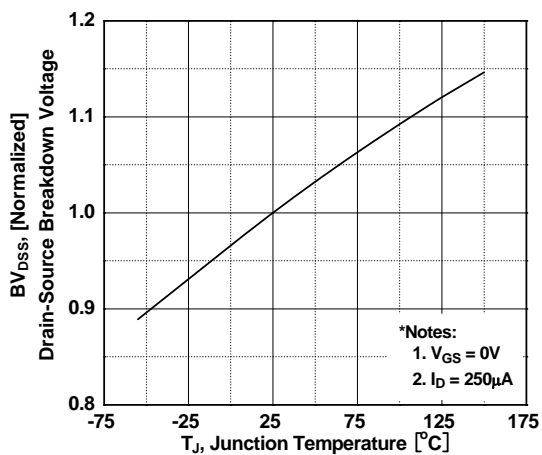


Figure 6. Gate Charge Characteristics

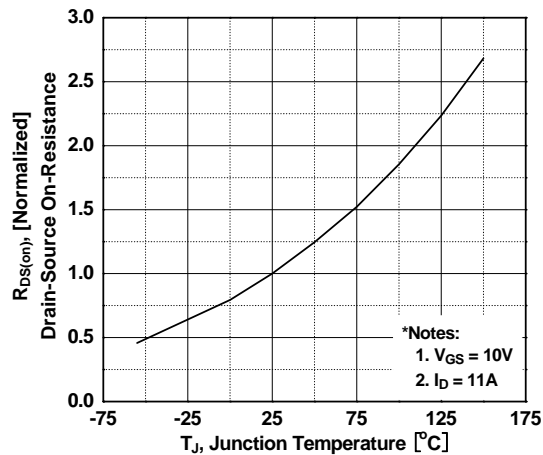


# Typical Performance Characteristics (Continued)

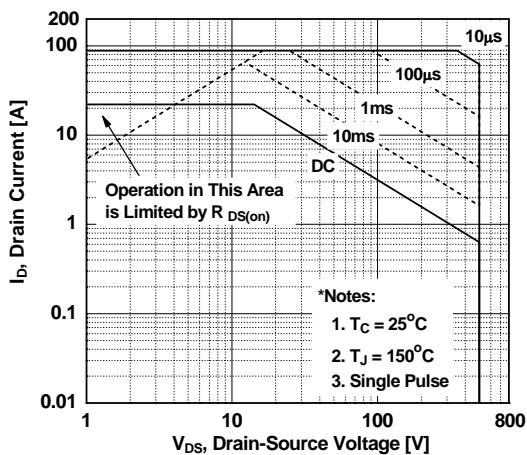
**Figure 7. Breakdown Voltage Variation vs. Temperature**



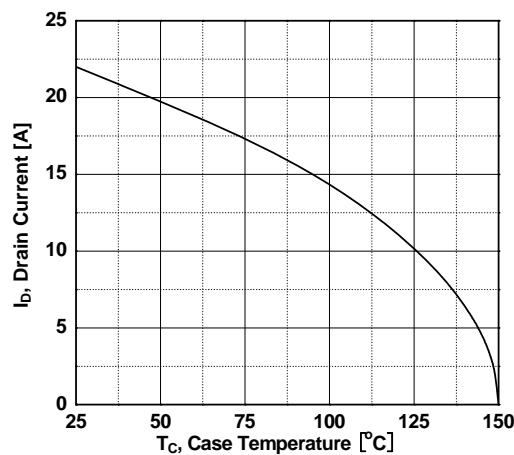
**Figure 8. On-Resistance Variation vs. Temperature**



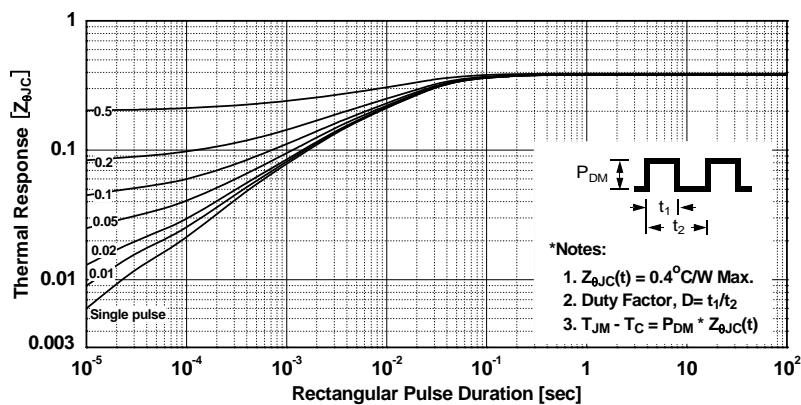
**Figure 9. Maximum Safe Operating Area - FDP22N50N**



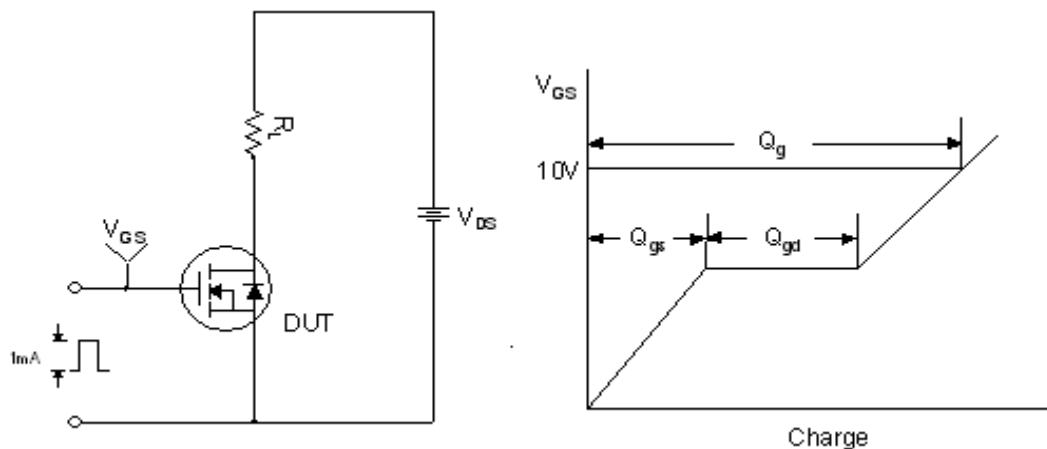
**Figure 10. Maximum Drain Current vs. Case Temperature**



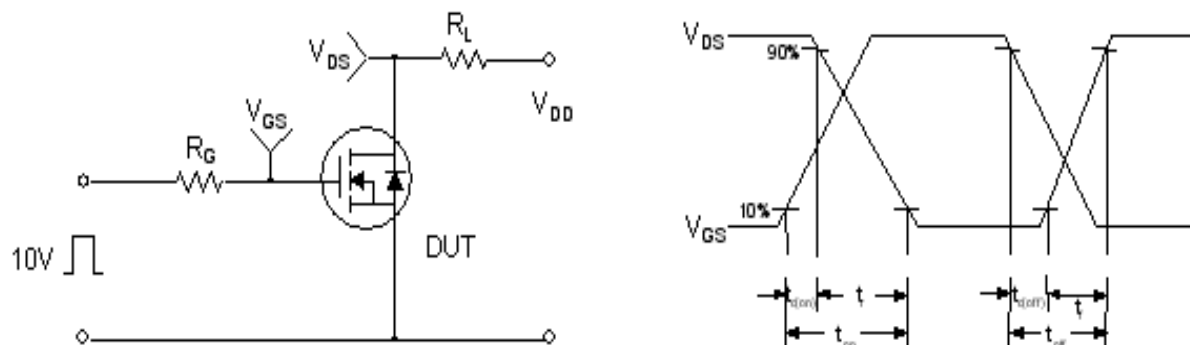
**Figure 10. Transient Thermal Response Curve - FDP22N50N**



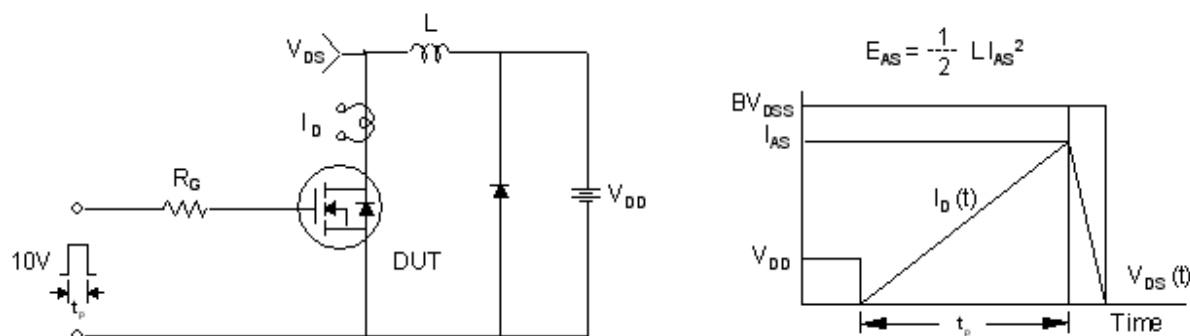
Gate Charge Test Circuit & Waveform



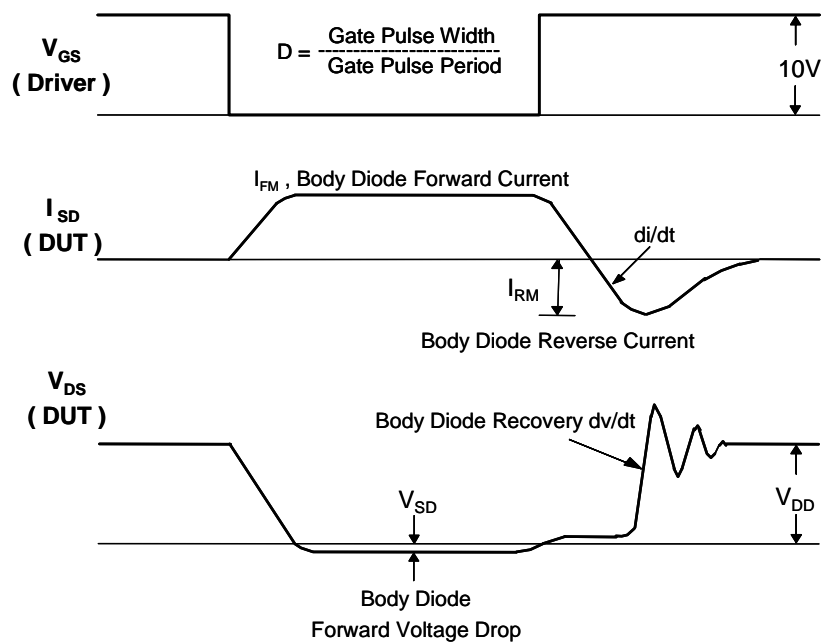
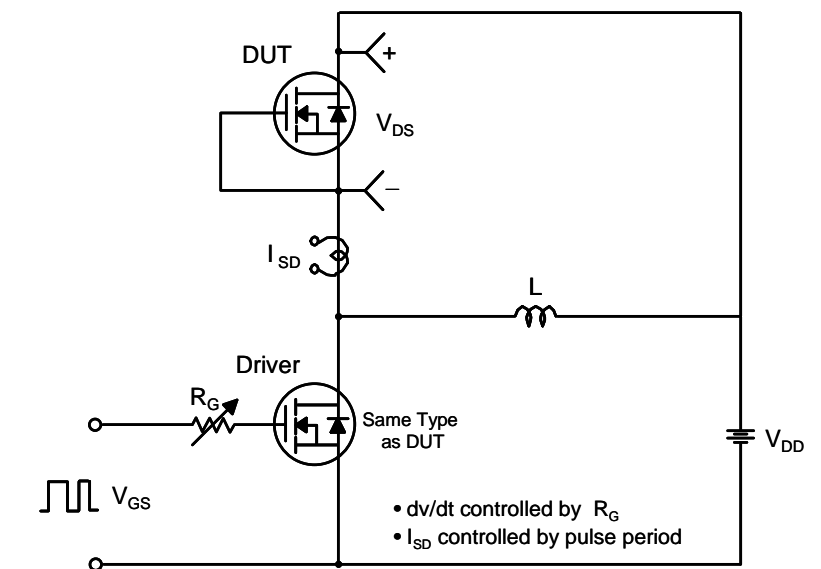
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

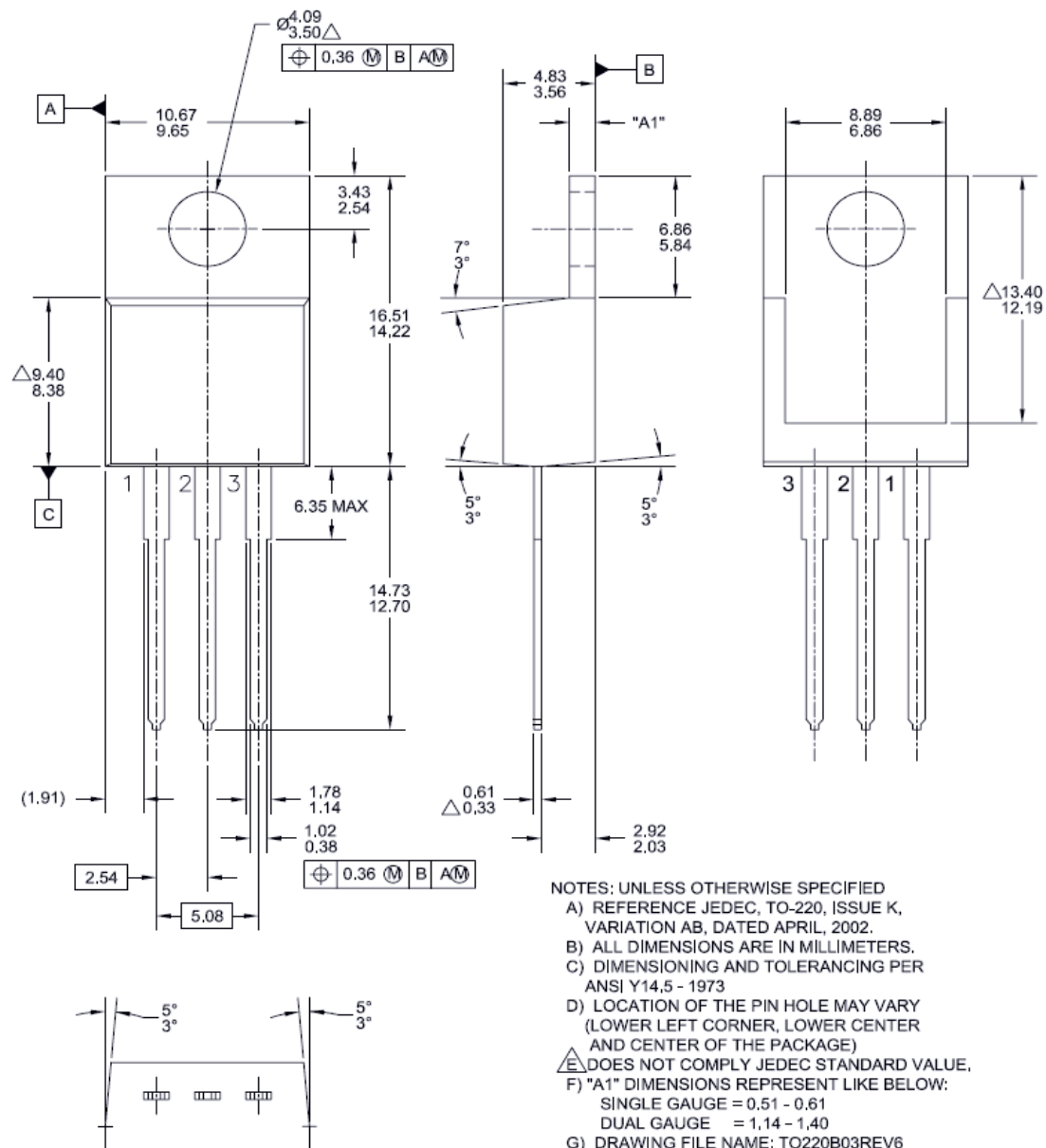


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions

## TO-220B03



Dimensions in Millimeters



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